

MDNA35P2200TG

tentative

High Voltage Standard Rectifier Module

= 2x 2200 V

35 A

V_F 1.1 V

Phase leg

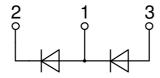
Part number

MDNA35P2200TG



Backside: isolated

F1 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments; - the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

20160425



MDNA35P2200TG

tentative

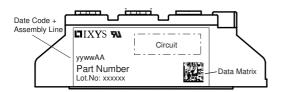
Rectifier					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse bloc	cking voltage	$T_{VJ} = 25^{\circ}C$			2300	V	
V_{RRM}	max. repetitive reverse blocking	ı voltage	$T_{VJ} = 25^{\circ}C$			2200	٧	
I _R	reverse current	V _R = 2200 V	$T_{VJ} = 25^{\circ}C$			20	μΑ	
		$V_R = 2200 V$	$T_{VJ} = 150$ °C			1.5	mΑ	
V _F	forward voltage drop	I _F = 35 A	$T_{VJ} = 25^{\circ}C$			1.15	V	
		$I_F = 70 \text{ A}$				1.34	٧	
		I _F = 35 A	$T_{VJ} = 125$ °C			1.10	V	
		$I_F = 70 \text{ A}$				1.35	٧	
I _{FAV}	average forward current	T _C = 100°C	T _{VJ} = 150°C			35	Α	
		rectangular d = 0.5					 	
V _{F0}	threshold voltage $T_{v,j} = 150$ °C				0.83	V		
r _F	slope resistance } for power	loss calculation only				7.3	mΩ	
R _{thJC}	thermal resistance junction to ca	ase				0.9	K/W	
R _{thCH}	thermal resistance case to heat	sink			0.20		K/W	
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			130	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			500	Α	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			540	Α	
		t = 10 ms; (50 Hz), sine	T _{VJ} = 150°C			425	Α	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			460	Α	
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.25	kA2s	
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			1.22	kA2s	
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			905	A ² s	
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			880	A²s	
C	junction capacitance	$V_{R} = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		19		pF	



MDNA35P2200TG

tentative

Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{VJ}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						76		g
M _D	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{T}}$	terminal torque				2.5		4	Nm
d _{Spp/App}	creepage distance on surface	Letriking distance through air			9.7			mm
$d_{\text{Spb/Apb}}$	creepage distance on surface	Striking distance through an			16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; lisoL ≤ 1 mA		4800			٧
.002		t = 1 minute			4000			٧



Part description

M = Module

D = Diode
N = High Voltage Standard Rectifier

A = (>= 2000V) 35 = Current Rating [A]

35 = Current rading,
P = Phase leg

2200 = Reverse Voltage [V]
TG = TO-240AA

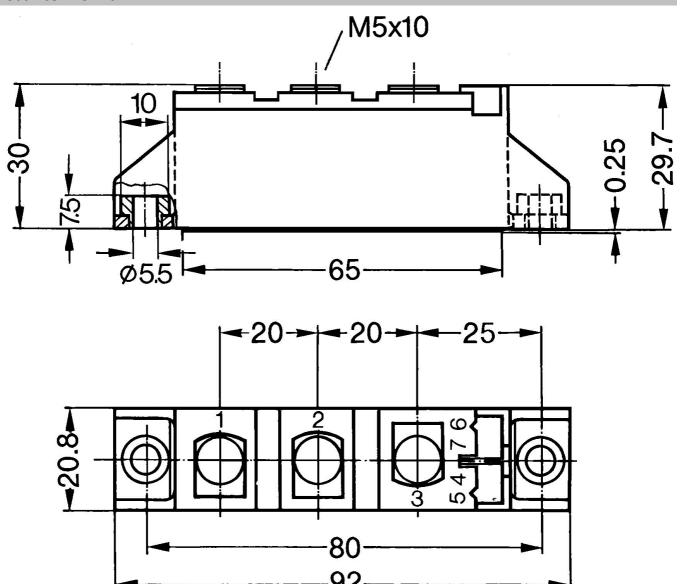
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDNA35P2200TG	MDNA35P2200TG	Box	36	

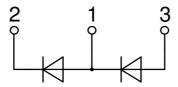
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$)—[R_o_]-	Rectifier		
V _{0 max}	threshold voltage	0.83		V
$R_{0 \; max}$	slope resistance *	6.1		$m\Omega$



tentative

Outlines TO-240AA





tentative



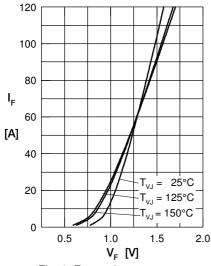


Fig. 1 Forward current versus voltage drop per diode

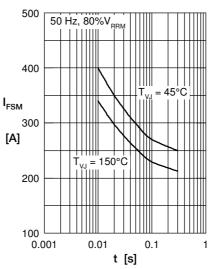


Fig. 2 Surge overload current vs. time per diode

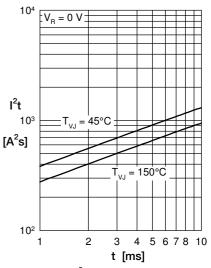


Fig. 3 I²t versus time per diode

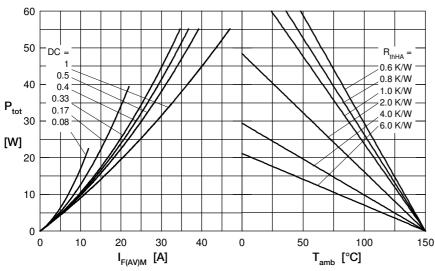


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

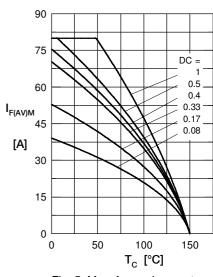


Fig. 5 Max. forward current vs. case temperature per diode

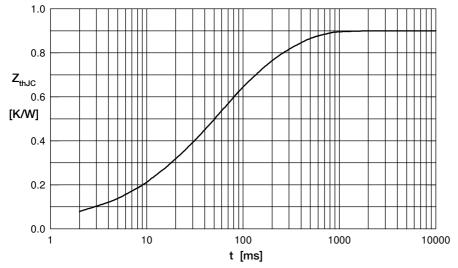


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for \boldsymbol{Z}_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.042	0.001
2	0.128	0.010
3	0.425	0.050
4	0.305	0.230